



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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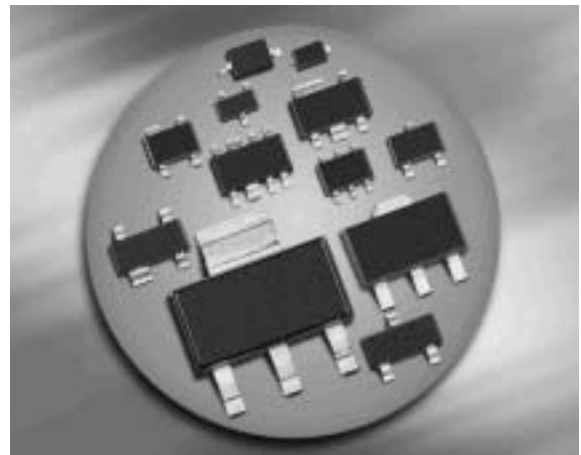
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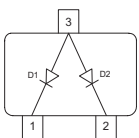


Silicon Low Leakage Diode

- Low-leakage applications
- Medium speed switching times
- Common anode configuration
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



BAW156



Type	Package	Configuration	Marking
BAW156	SOT23	common anode	JZs

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Peak reverse voltage	V_{RM}	85	
Forward current	I_F	200	mA
Non-repetitive peak surge forward current	I_{FSM}		A
$t = 1 \mu\text{s}$		4.5	
$t = 1 \text{s}$		0.5	
Total power dissipation $T_s \leq 31^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾ BAW156	R_{thJS}	≤ 360	K/W

¹⁾Pb-containing package may be available upon special request

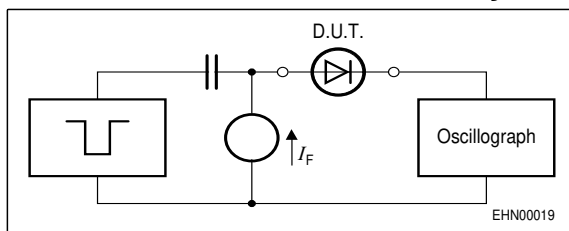
²⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(BR)}$	85	-	-	V
Reverse current $V_R = 75 \text{ V}$ $V_R = 75 \text{ V}, T_A = 150^\circ\text{C}$	I_R	-	-	5 80	nA
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 150 \text{ mA}$	V_F	-	-	900 1000 1100 1250	mV

AC Characteristics

Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	2	-	pF
Reverse recovery time $I_F = 10 \text{ mA}, I_R = 10 \text{ mA}$, measured at $I_R = 1 \text{ mA}$, $R_L = 100 \Omega$	t_{rr}	-	0.6	1.5	μs

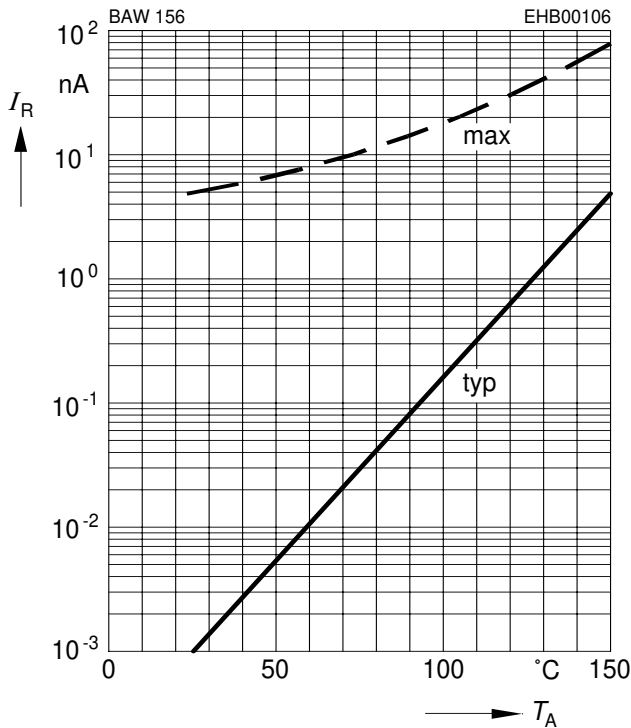
Test circuit for reverse recovery time


Pulse generator: $t_p = 10 \mu\text{s}$, $D = 0.05$, $t_r = 0.6 \text{ ns}$,
 $R_i = 50 \Omega$

Oscilloscope: $R = 50 \Omega$, $t_r = 0.35 \text{ ns}$, $C \leq 1 \text{ pF}$

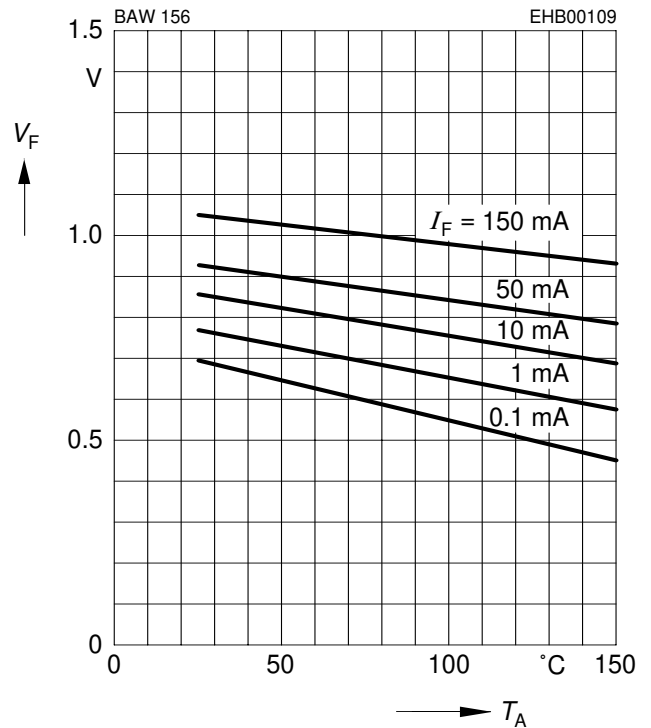
Reverse current $I_R = f(T_A)$

$V_R = 70V$



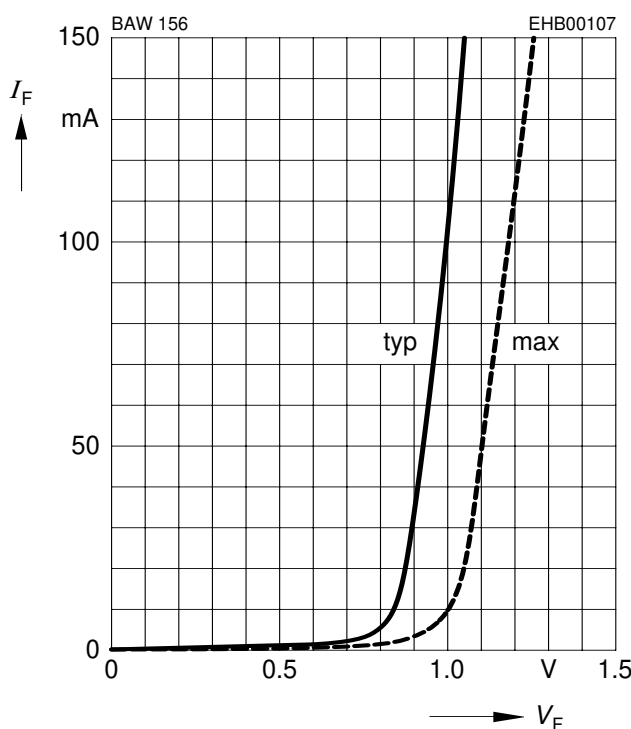
Forward Voltage $V_F = f(T_A)$

$I_F = \text{Parameter}$



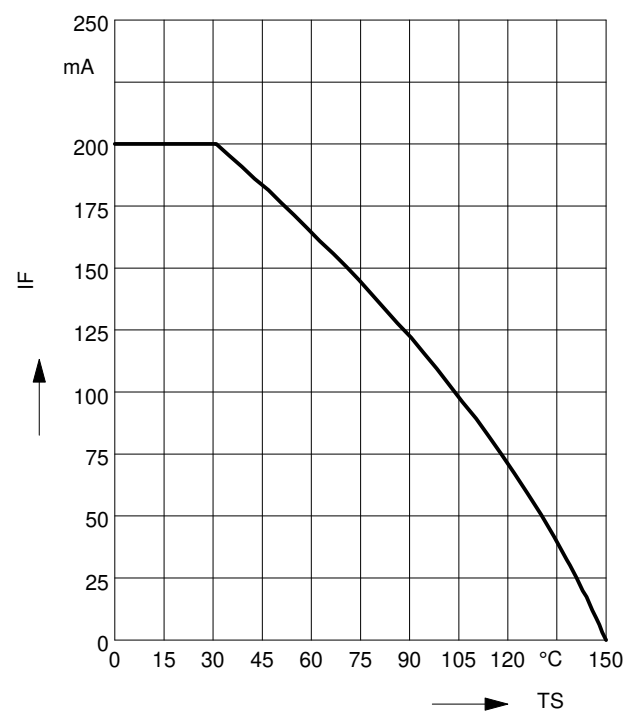
Forward current $I_F = f(V_F)$

$T_A = 25^\circ C$

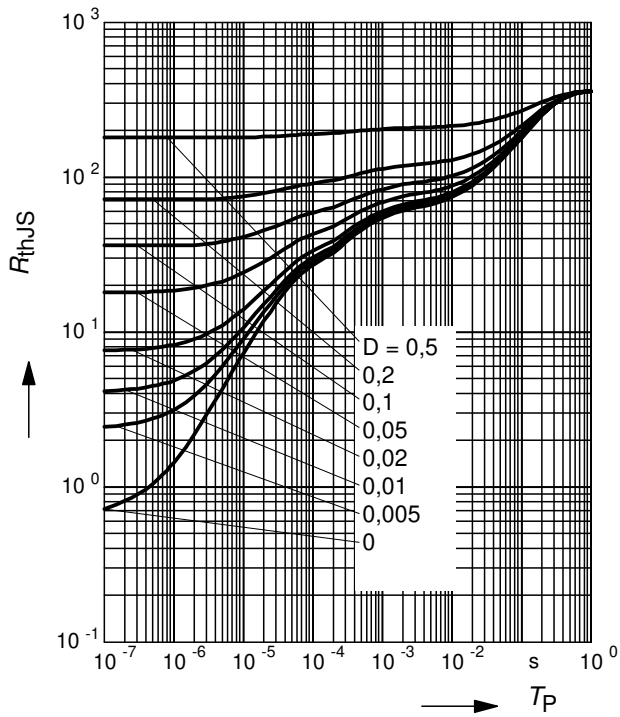


Forward current $I_F = f(T_S)$

BAW156

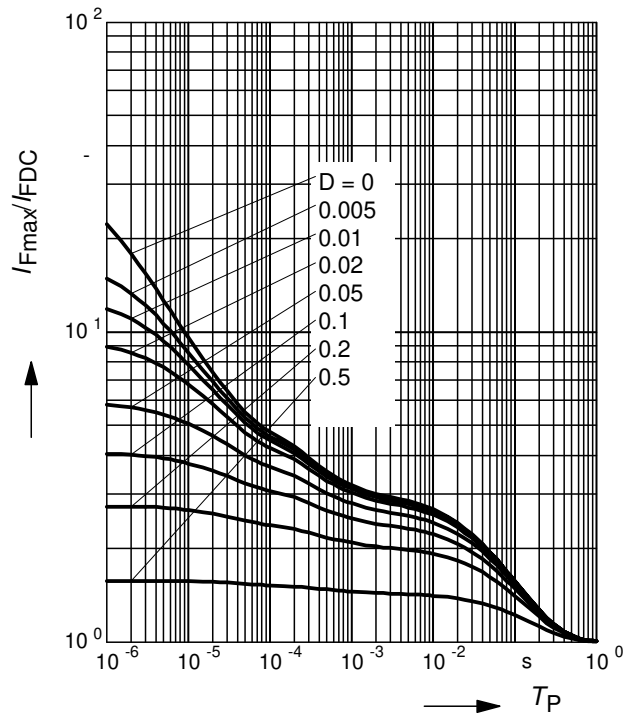


Permissible Puls Load $R_{thJS} = f(t_p)$

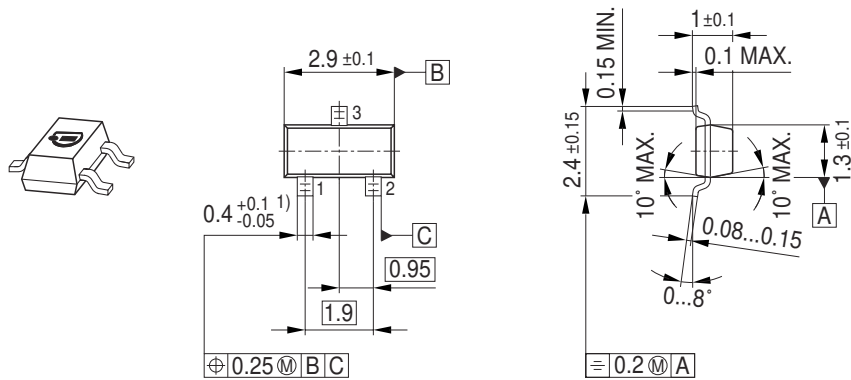


Permissible Pulse Load

$I_{Fmax}/I_{FDC} = f(t_p)$

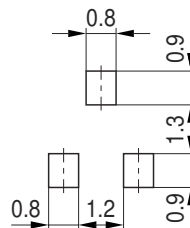


Package Outline

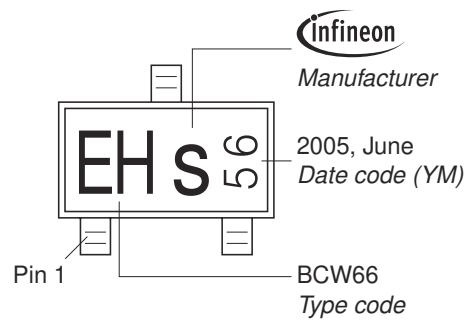


1) Lead width can be 0.6 max. in dambar area

Foot Print

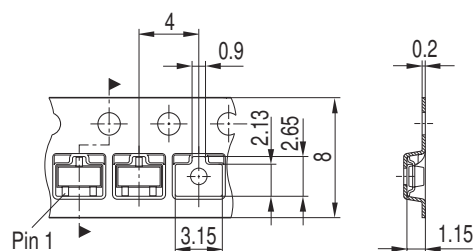


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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